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INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT

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				Complaint If Known	
				Application Number	10/077,784
				Filing Date	February 20, 2002
				First Named Inventor	Terry L. Gilton
				Art Unit	2818
				Examiner Name	Not Yet Assigned PHAN
Sheet	1	of	1	Attorney Docket Number	M4065.0482/P482

## U. S. PATENT DOCUMENTS

Examiner Initials*	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code <sup>3</sup> (# known)			
TP	A	5,883,827	3/16/1999	Morgan	

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Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>4</sup>
		Country Code <sup>3</sup> -Number-Kind Code <sup>4</sup> (# known)				

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## OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

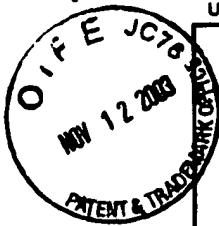
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AL					
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AO					

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		Country Code <sup>3</sup> -Number <sup>4</sup> -Kind Code <sup>5</sup> (if known)				
TP	BA	WO 02/21542	03/14/2002	Kozicki et al.		
TP	BB	WO 00/48196	08/17/2000	Kozicki et al.		
TP	BC	WO 97/48032	12/18/1997	Kozicki et al.		
TP	BD	WO 99/28914	06/10/1999	Kozicki et al.		

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Sheet 2 of 8 Attorney Docket Number M4065.0482/P482

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OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS		
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				Filing Date February 20, 2002
				First Named Inventor Terry L. Gilton
				Group Art Unit 2818
				Examiner Name Not Yet Assigned PHAN
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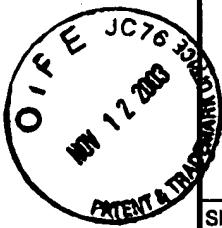
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				Application Number	10/077,784
				Filing Date	February 20, 2002
				First Named Inventor	Terry L. Gilton
				Group Art Unit	2818
				Examiner Name	Not Yet Assigned PHAN
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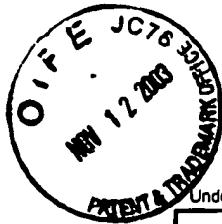
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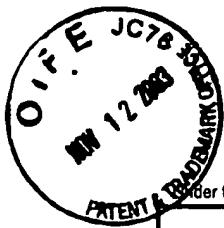
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				First Named Inventor	Gilton, et al.
				Art Unit	2818
				Examiner Name	T. Phan
Sheet	1	of	4	Attorney Docket Number	M4065.0482/P482

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## INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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				Complete if Known	
				Application Number	10/077,784
				Filing Date	February 20, 2002
				First Named Inventor	Gilton, et al.
				Art Unit	2818
				Examiner Name	T. Phan
Sheet	2	of	4	Attorney Docket Number	M4065.0482/P482

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Sheet	3	of	4	Attorney Docket Number
				M4065.0482/P482

**FOREIGN PATENT DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document Country Code <sup>2</sup> -Number <sup>3</sup> -Kind Code <sup>4</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>5</sup>
TP	BA	56126916	10/19981	Akira et al.		

Examiner Signature	Trong Phan	Date Considered	1/22/04
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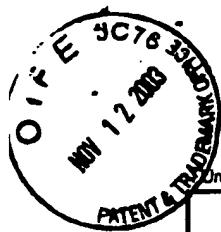
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Sheet	4	of	4	Attorney Docket Number	M4065.0482/P482

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS				
Examiner Initials	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.		T <sup>2</sup>
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Examiner Signature	Trong Phan	Date Considered	1/22/04
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<p>Application Number</p>		<p><b>10/077,784</b></p>				
<p>Filing Date</p>		<p><b>February 20, 2002</b></p>				
<p>First Named Inventor</p>		<p><b>Terry L. Gilton</b></p>				
<p>Art Unit</p>		<p><b>2818</b></p>				
<p>Examiner Name</p>		<p><b>Not Yet Assigned</b> <i>PHAN</i></p>				
Sheet	1	of	1	Attorney Docket Number	<p><b>M4065.0482/P482</b></p>	

## U.S. PATENT DOCUMENTS

U.S. PATENT DOCUMENTS					Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	
Examiner Initials*	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document		
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## FOREIGN PATENT DOCUMENTS

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		Country Code <sup>2</sup> Number <sup>3</sup> Kind Code <sup>4</sup> (if known)			

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Examiner Signature	Trong Phan	Date Considered	1/22/04
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